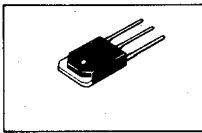


No.1225

2SD1399



NPN Triple Diffused Planar Type Silicon Transistor
For Horizontal Output (Built-in Damper Diode)

Features:

- High Breakdown Voltage and High Reliability.
- High Switching Speed.
- Capable of being mounted easily due to one-point fixing type plastics mold package.

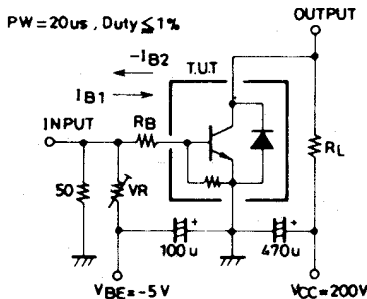
Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	VCBO	1500	V
Collector to Emitter Voltage	VCEO	800	V
Emitter to Base Voltage	VEBO	7	V
Collector Current	IC	6	A
Peak Collector Current	icp	16	A
Collector Dissipation	PC	Tc=25°C	50 W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

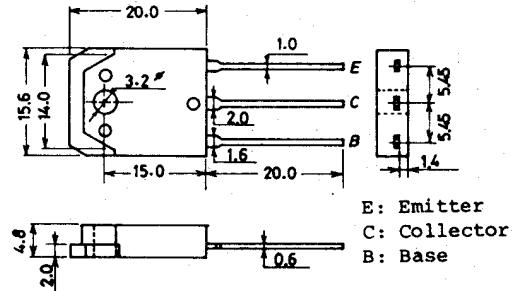
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	ICBO	VCB=800V, IE=0			10	uA
Emitter Cutoff Current	IEBO	VEB=4V, IC=0	40		130	mA
DC Current Gain	hFE	VCE=5V, IC=1A	8			
Gain Bandwidth Product	fT	VCE=10V, IC=1A		3		MHz
C-E Saturation Voltage	VCE(sat)	IC=5A, IB=1A			5	V
B-E Saturation Voltage	VBE(sat)	IC=5A, IB=1A			1.5	V
C-B Breakdown Voltage	V(BR)CBO	IC=5mA, IE=0	1500			V
C-E Breakdown Voltage	V(BR)CEO	IC=100mA, RBE=∞	800			V
E-B Breakdown Voltage	V(BR)EBO	IE=200mA, IC=0	7			V
Diode Forward Voltage	VF	IEC=6A			2	V
Fall Time	tf	IC=5A, IB1=1A, IB2=-2A VCC=200V, RL=40ohm			0.7	us

Switching Time Test Circuit



Case Outline 2022 (unit:mm)



These specifications are subject to change without notice.

TOKYO SANYO ELECTRIC CO., LTD. SEMICONDUCTOR DIVISION
15-13, 6-CHOME, SOTOKANDA, CHIYODA-KU, TOKYO 101 JAPAN